BOUSKILA LAURENE 949271543



- 1. For an RG058-model coaxial cable, given with a=0.9 mm, b= 2.95 mm, ε_r =2.3, find:
- (a) The characteristic impedance and wave velocity in the TEM mode.

(b) The propagation time of a 1-ns pulse in a 10-m long section of this coaxial cable.

- (c) The phase accumulation vs. frequency (the term kz in Eqs. 1a, b), in the range 0-6 GHz.
- (d) How the results above would be changed for b= 4 mm and for ε_r = 4?

- 2. For a rectangular waveguide, given with a=100 mm, b= 50 mm, find:
- (a) The dispersion relation in the TE10 mode, also in a graph as in Fig. 3.

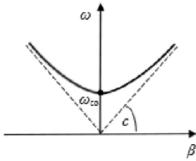


Figure 3: The dispersion relation of a rectangular waveguide in the TE10 mode.

for the first mode:

| Ki0 = √ μεω² - (π/α)²
| Bi0 = √ (Ψ)² - (π/α)²
| Γ/α)²

(b) The cutoff frequency and wavelength (how the latter relates to the waveguide width?)

$$\omega_{c} = \frac{\pi c}{a\sqrt{er}} = 2\pi f_{c}$$

$$\int_{c=1}^{e} \frac{1}{2\pi} f_{c}$$

$$\int_{c=1}^{e} \frac{1}{2\pi} f_{c}$$

$$\int_{c=1}^{e} \frac{1}{2\pi} f_{c}$$

$$\int_{c=1}^{e} \frac{1}{2\pi} f_{c}$$

$$\int_{c=2}^{e} \frac{1}{2\pi} f_{c}$$

$$\int_{c=3}^{e} \frac{1}{2\pi} f_{c}$$

(c) Repeat (a) and (b) for the second higher mode(s).

ta) and (b) for the second higher mode(s).

For the 2nd higher were =
$$T \in 20$$
; $\beta = \sqrt{(\frac{1}{6})^2 - (\frac{1}{6})^2}$
 $\omega_0 = 2\pi c/a = 6\pi \cdot 10^9$
 $-\beta_0 = \frac{\omega_0}{2\pi} = 3GH_2$
 $\lambda = \frac{c}{f_0} = 0$, $\beta = 100$ m/m

(d) This waveguide is now truncated to a length of 1 m with perfect mirrors, to form a rectangular cavity (as in Fig. 4). What would be the resonance frequencies of this cavity? Where would these frequencies appear on the dispersion diagram?

$$\omega_{n} = c\sqrt{(\frac{\pi}{4})^{2} + (n\frac{\pi}{4})^{2}} \quad L=1 m$$

$$F(9 \ 4) \rightarrow n=3 \quad \omega_{3} = 3\cdot10^{8} \sqrt{(10\pi)^{2} + (3\pi)^{2}} \cdot Q, 8464724$$

3. Present the general form of a 2-port scattering matrix, and explain its various terms.

Scattering matrix may be helpful to know that as voltage and current are to electrical circuit analysis, S parameters are to microwave network analysis. S parameter are formed from ratios of reflected and incident voltage wave amplitudes.

$$\begin{bmatrix} V^{-} \end{bmatrix} = \begin{bmatrix} S \end{bmatrix} \cdot \begin{bmatrix} V^{+} \end{bmatrix}$$

$$Z_{0} \qquad \qquad \downarrow Z_{0}$$

$$V_{1}^{+} \swarrow \swarrow \qquad \downarrow Z_{0}$$

$$V_{1}^{-} \swarrow \swarrow \qquad \downarrow Z_{0}$$

 S_{11} can be written as the ratio of reflected wave and incident wave.

$$S_{11} = \frac{V_1^-}{V_1^+}$$
 , $V_2^+ = 0$

Therefore we obtain $S_{11} = \Gamma_{11}$ which is the voltage reflection coefficient at port 1.

$$S_{21} = \frac{V_2^-}{S_1^+}$$
 , $V_2^+ = 0$

With matched load at port 2 so $V_2^+ = 0$ then $S_{21} = \Gamma_{21}$ which is the voltage transmisson coefficient from port 1 to 2.

4. Describe the VNA functions in general, and explain its calibration procedure.

Vector Network Analyzer (VNA) is an instrument that measures the network parameters of electrical networks. VNA commonly measure s—parameters because reflection and transmission of electrical networks are easy to measure at high frequencies, but there are other network parameter sets such as y-parameters, z-parameters, and h-parameters. Network analyzers are often used to characterize two-port networks such as amplifiers and filters.

5. What would you expect to get as S_{11} for the cavity given in Question 2(c) above?

Expect to get S₁₁=0 since input port is matched therefore there is no reflected wave.

- 6. The formulae in Eqs. (6, 7) enable the analysis of a given micro-strip line (given the dimensions and dielectric fill, one can find the effective impedance and wave velocity). However, for the design of a micro-strip line, the desired impedance and wave velocity are known, but the line dimensions and dielectric fill shall be found. Find alternative equations and graphs for the design of a micro-strip line.
- 7. Given a dielectric fill for a micro-strip line of ϵ_r = 2.1 and h=82 mm, find the strip width w in order to realize a 50 Ω micro-strip line. What would be eff ϵ in this case?

and for w/h > 1 by

$$\varepsilon_{\rm eff} = \frac{\varepsilon_{\rm r} + 1}{2} + \frac{\varepsilon_{\rm r} - 1}{2 \cdot \sqrt{1 + 12h/w}} \,, \qquad \qquad Z_c = \frac{120\pi}{\sqrt{\varepsilon_{\rm eff}} \left[\frac{w}{h} + 1.393 + \frac{2}{3} \ln\left(\frac{w}{h} + 1.444\right) \right]} \,.$$

$$w = 3.208 * 8.2 \times 10^{-3} = 0.026[m]$$

 $\varepsilon_{eff} = 1.802$